



Design of CMOS Operational Amplifier

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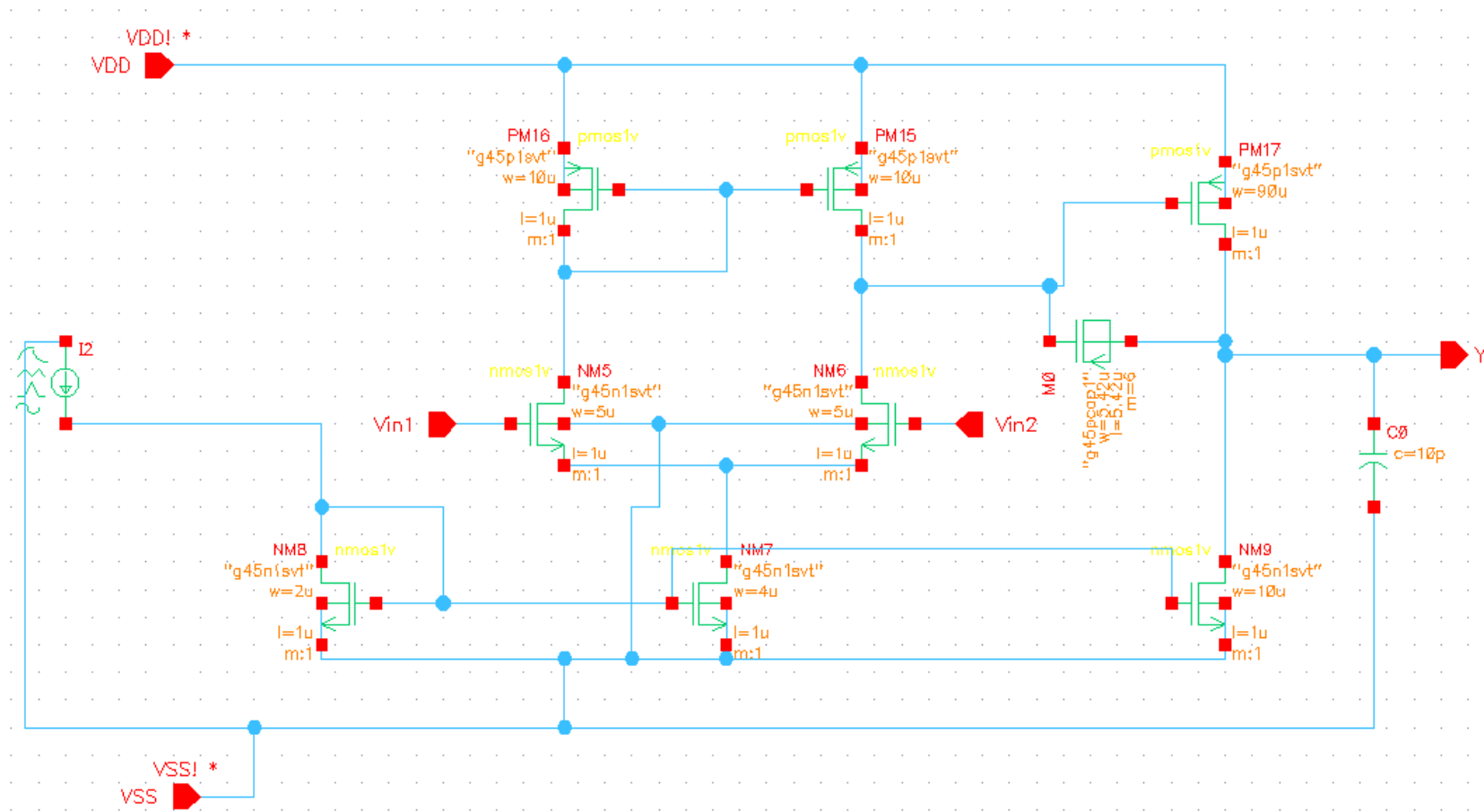
Agenda

- ▶ Specification
- ▶ Schematic and Initial approach
- ▶ Equations
- ▶ In a Search of design parameters
- ▶ Parameters
- ▶ Other simulations
- ▶ Layout
- ▶ Outcome

Specifications

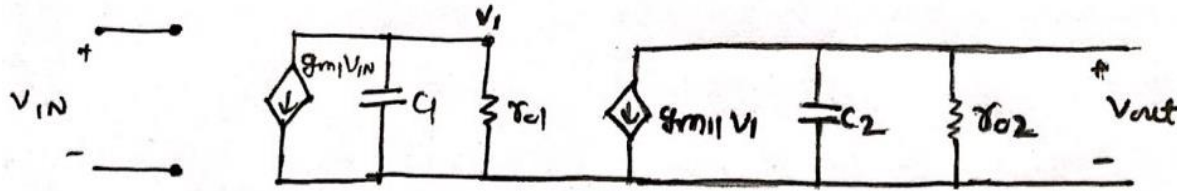
Parameter	Value
VDD	1V
Temperature Range	0°C to 100 °C
Capacitive Load	10pF
Reference Current	10 μ A
CMRR	> 50 dB
Open Loop Gain	> 50 dB
Phase Margin	> 50 dB
Gain Bandwidth	> 5 MHz
Slew Rate	> 8 V/ μ s
ICMR	Withing 200mV of VDD and VSS
Output Swing	Withing 5mV of both the rails

Schematic



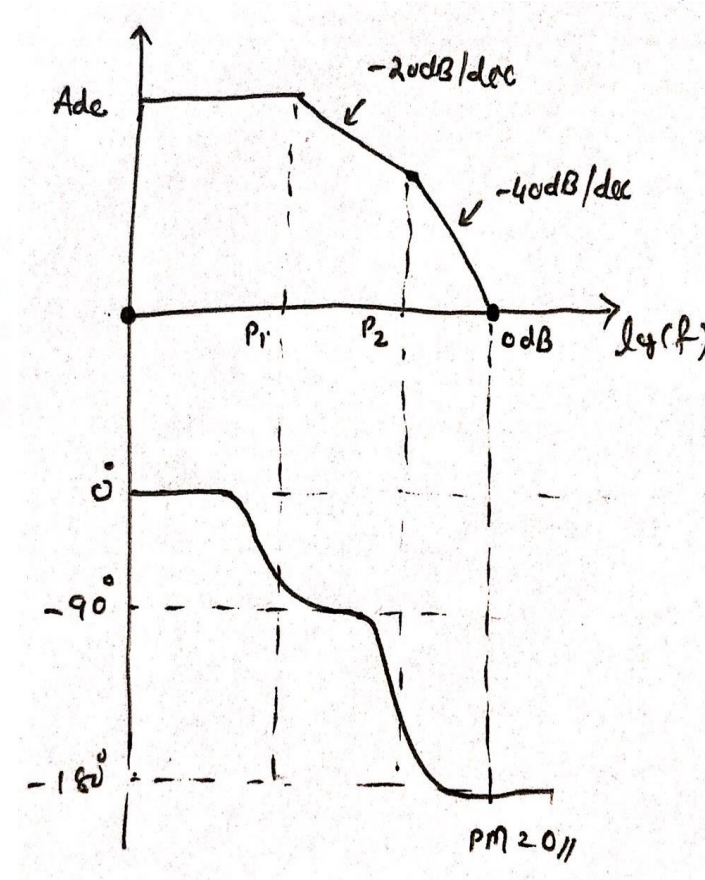
Initial approach

- Small signal model and bode analysis



Small signal model

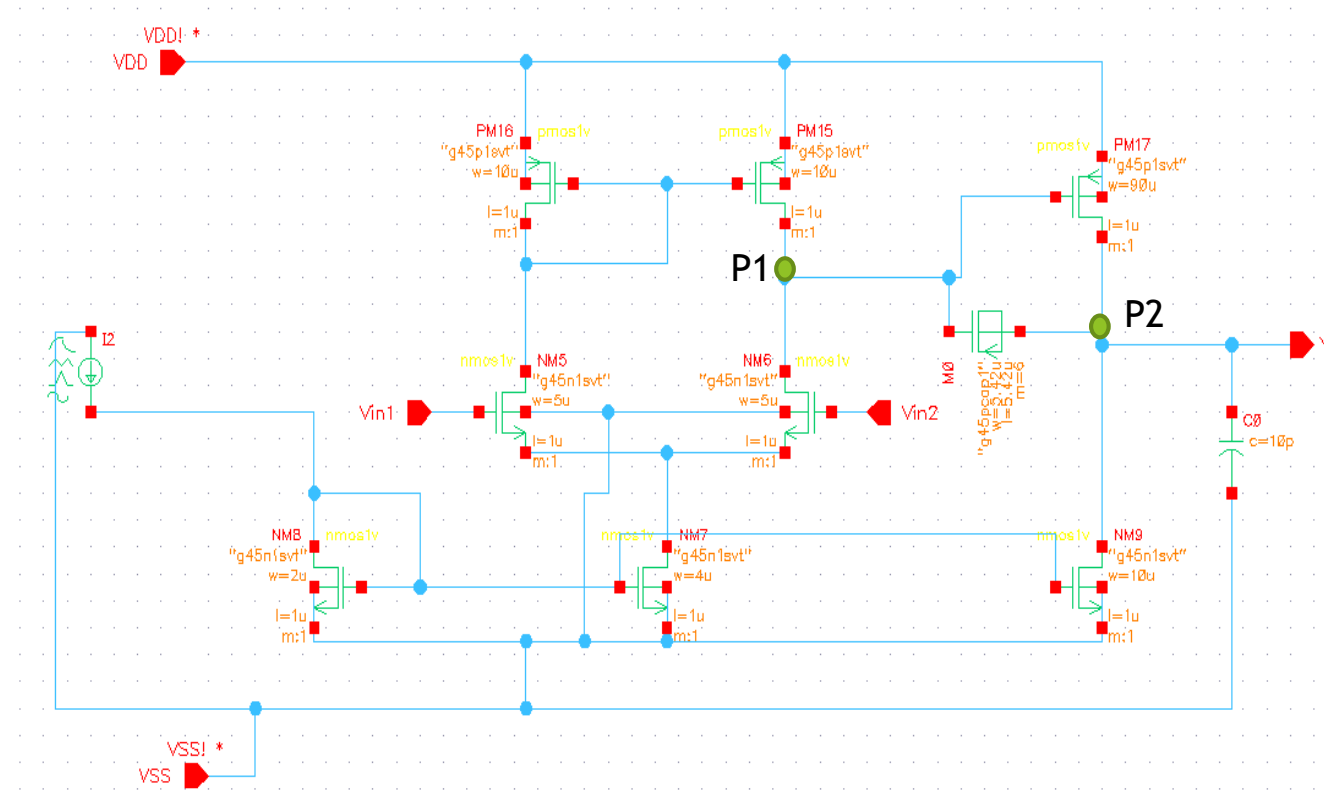
- Pole location by inspection
- $P1 = 1/r_{o1}C1$ & $P2 = 1/r_{o2}C2$
- Ideas
 - To improve PM, change the position of poles.



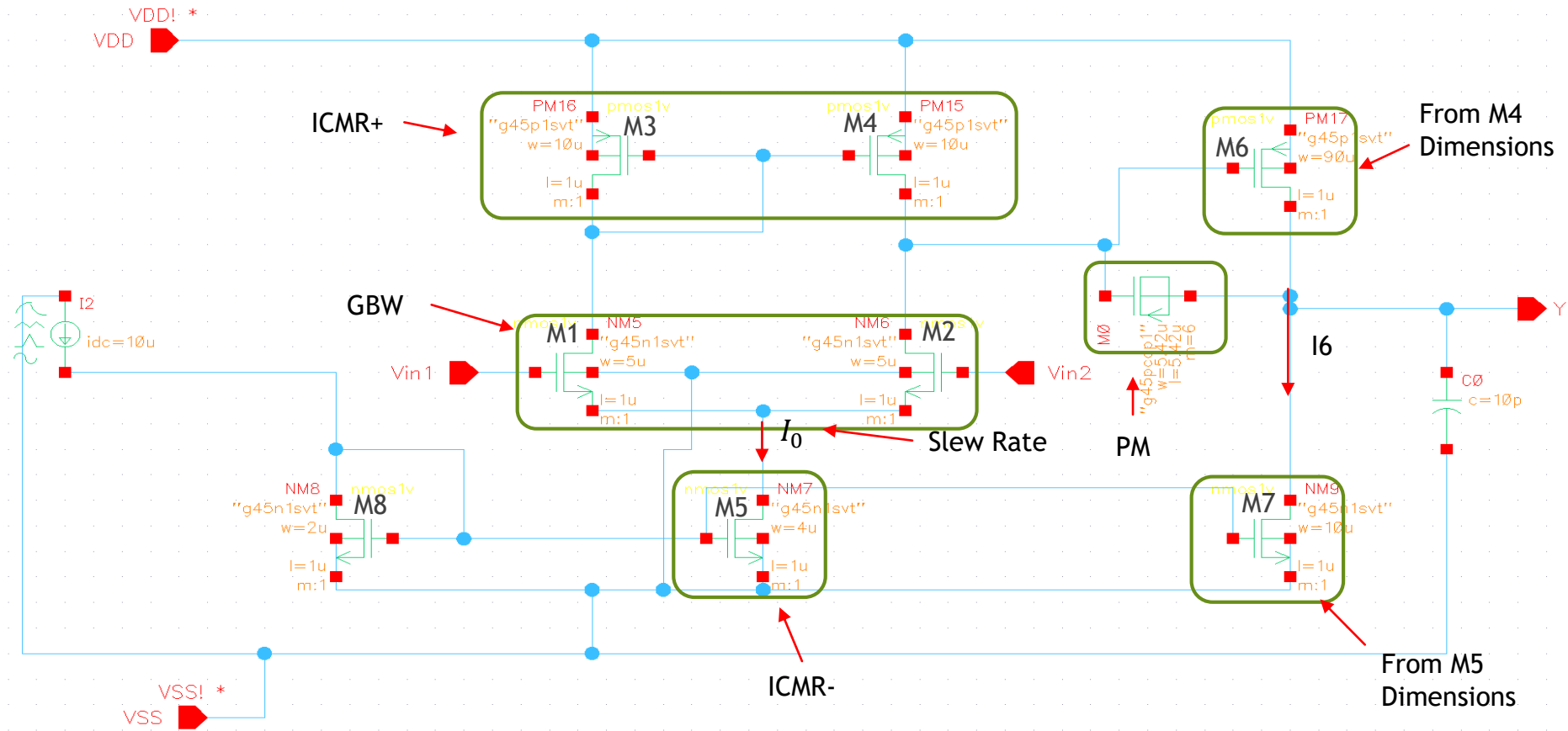
Bode Plot

Equations

- ▶ $P1 = 1/g_{m2} R_1 R_2 C_c$
- ▶ $P2 = g_{m2}/C_2$
- ▶ $Z = g_{m2}/C_c$
- ▶ $A_{dc} = g_{m1} R_1 g_{m2} R_2$
- ▶ $GBW = DC \text{ gain} \times P1$
- ▶ $GBW = g_{m1}/C_c$
- ▶ $Slew \text{ Rate} = I_0/C_c$



In a Search of design parameters



Parameters obtained

MOSFET	W/L ratio (Initial)	W/L ratio (Final)
M1 , M2	4/1	5/1
M3 , M4	14/1	15/1
M5	3/1	3/1
M6	85/1	90/1
M7	10/1	10/1

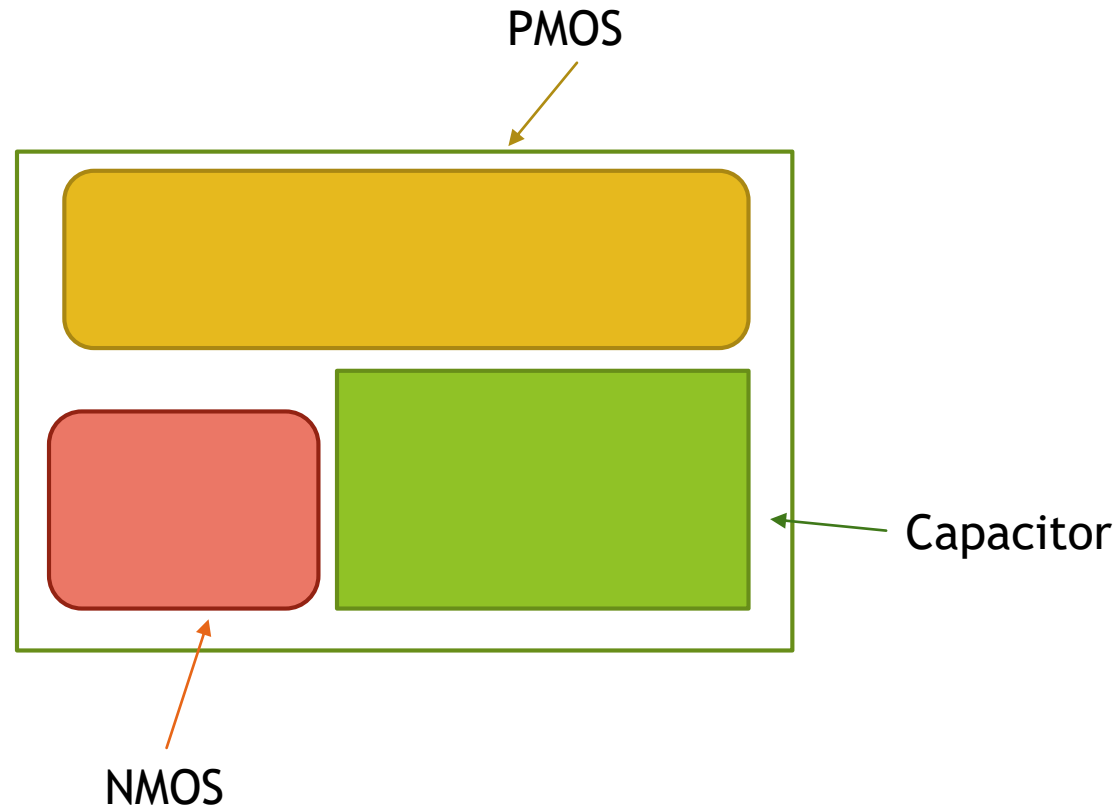
- Simulation done in Cadence 45 nm technology
- $C_c = 2.5 \text{ pF}$ and $I_0 = 20 \mu\text{A}$

Other simulations

- ▶ Process corners
- ▶ Temperature variations (0 to 100 °C)
- ▶ Monte Carlo analysis for 30 runs

Layout

- ▶ Interdigitated
- ▶ Fingers
- ▶ Multipliers
- ▶ Dummy
- ▶ Area = $16 \times 28 \mu m^2$



Outcome

- ▶ Gain = 55 dB
- ▶ Phase margin = 52 dB
- ▶ Bandwidth = 5.1 MHz
- ▶ CMR+ = 0.75 V, CMR- = 0.24 V
- ▶ Slew rate = 8.1 V/ μ s
- ▶ CMRR = 53 dB
- ▶ Power consumed = 85 μ W
- ▶ Layout Area = 448 μ m²